TIGER ELECTRONIC CO.,LTD

Product specification

Complementary Silicon Power Ttransistors

MJD41C / 42C

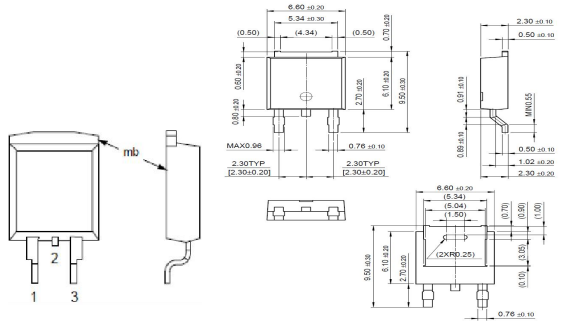
RoHS COMPLIANT

DESCRIPTION

It is intented for use in power
amplifier and switching applications.

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	±100	V
Collector-Emitter Voltage	V_{CEO}	±100	V
Emitter-Base Voltage	V_{EBO}	±6.0	V
Collector Current	I_C	±5.0	A
Base Current	I_B	±2.0	A
Total Dissipation at	P_{tot}	30	W
Max. Operating Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~150	°C



1：B
2：C
3：E

TO-252

ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector Cut-off Current	I_{CEO}	V_{CB}= ±100V, I_E=0	—	—	±10	uA
Emitter Cut-off Current	I_{EBO}	V_{EB}= ±5.0V, I_C=0	—	—	±10	uA
Collector-Emitter Sustaining Voltage	V_{CEO}	I_C= ±10mA, I_B=0	±100	—	—	V
DC Current Gain	$h_{FE(1)}$	V_{CE}= ±4.0V, I_C= ±0.3A	30	—	—	
	$h_{FE(2)}$	V_{CE}= ±4.0V, I_C= ±3.0A	25	—	100	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C= ±5.0A,I_B= ±500mA	—	—	±1.5	V
Base-Emitter on Voltage	$V_{BE(on)}$	V_{CE}= ±4.0V,I_C= ±5.0A	—	—	±2.0	V
Current Gain Bandwidth Product	f_T	V_{CE}= ±10V,I_C= ±500mA	3.0	—	—	MHz